

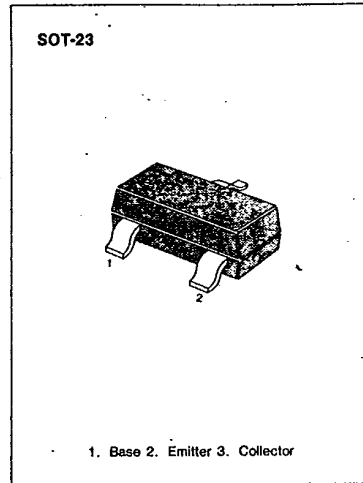
MMBT6428 NPN EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CE0}	50	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	I _C	200	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT5088 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _C =0.1mA, I _E =0	60		V
Collector-Emitter Breakdown Voltage	BV _{CE0}	I _C =1.0mA, I _B =0	50		V
Collector Cutoff Current	I _{CB0}	V _{CB} =30V, I _E =0		0.01	μA
Collector Cutoff Current	I _{CE0}	V _{CE} =30V, I _B =0		0.1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} =5.0V, I _C =0		0.01	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =0.01mA	250		
		V _{CE} =5V, I _C =0.1mA	250	650	
		V _{CE} =5V, I _C =1.0mA	250		
		V _{CE} =5V, I _C =10mA	250		
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C =10mA, I _B =0.5mA		0.2	V
		I _C =100mA, I _B =5mA		0.6	V
Base-Emitter On Voltage	V _{BE} (on)	I _C =1mA, V _{CE} =5V	0.56	0.66	V
Current Gain-Bandwidth Product	f _T	I _C =1.0mA, V _{CE} =5V	100	700	MHz
		f=100MHz			
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0 f=1.0MHz		3	pF

Marking

